

2SD2066

Silicon NPN triple diffusion planar type

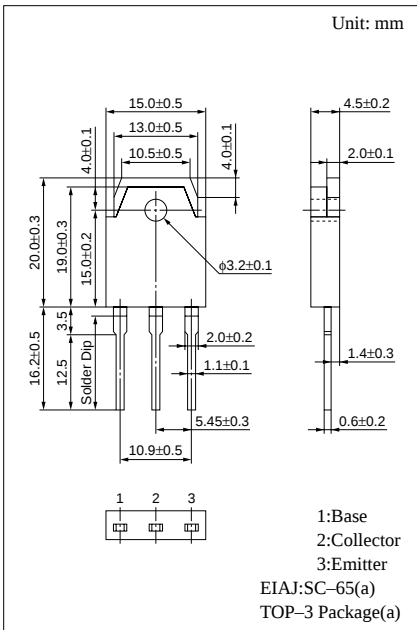
For high power amplification
Complementary to 2SB1373

■ Features

- High breakdown voltage: $V_{CEO} = 160V$ (min.)
- Extremely satisfactory linearity of the forward current transfer ratio h_{FE}
- High transition frequency f_T
- Wide area of safe operation (ASO)

■ Absolute Maximum Ratings ($T_C=25^\circ C$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	160	V
Collector to emitter voltage	V_{CEO}	160	V
Emitter to base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	20	A
Collector current	I_C	12	A
Collector power dissipation	P_C	$T_C=25^\circ C$	W
		$T_a=25^\circ C$	
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

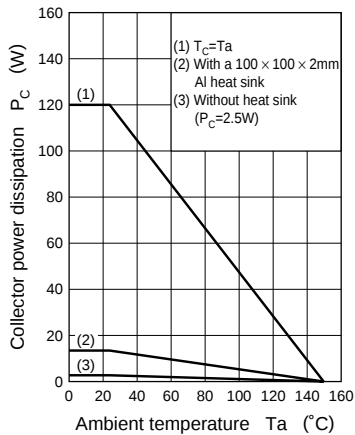
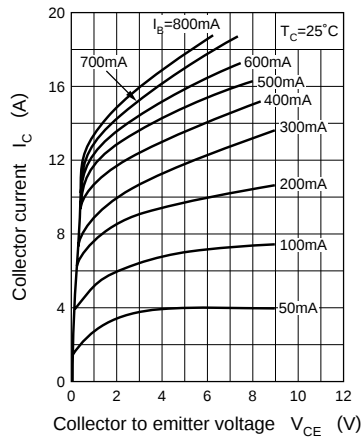
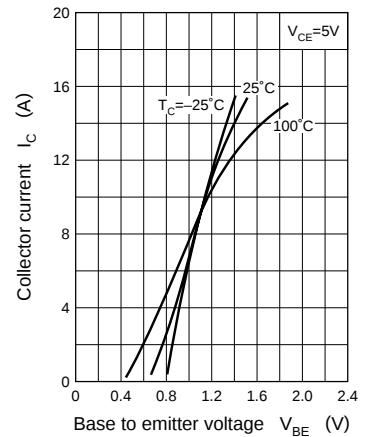
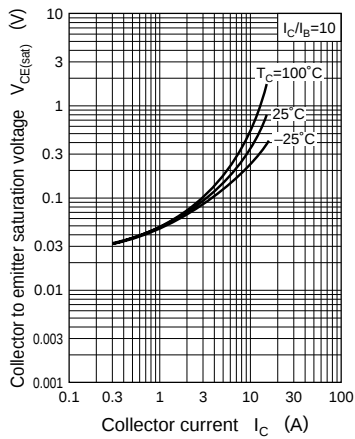
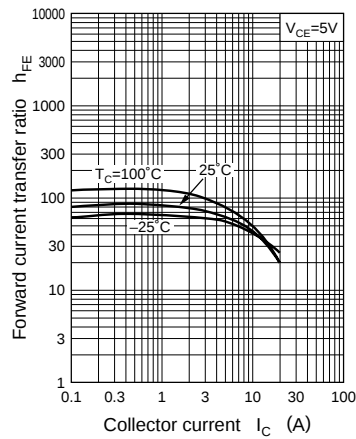
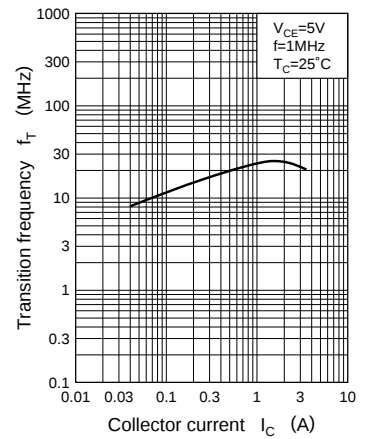
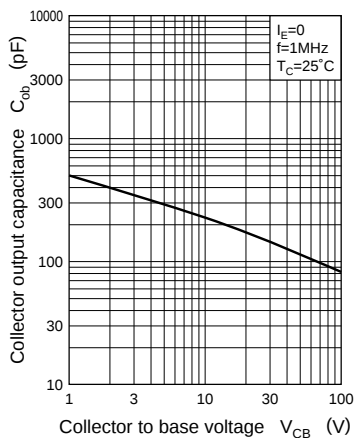


■ Electrical Characteristics ($T_C=25^\circ C$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 160V, I_E = 0$			50	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 3V, I_C = 0$			50	μA
Forward current transfer ratio	h_{FE1}	$V_{CE} = 5V, I_C = 20mA$	20			
	h_{FE2}^*	$V_{CE} = 5V, I_C = 1A$	60		200	
	h_{FE3}	$V_{CE} = 5V, I_C = 8A$	20			
Base to emitter voltage	V_{BE}	$V_{CE} = 5V, I_C = 8A$			1.8	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 8A, I_B = 0.8A$			2.0	V
Transition frequency	f_T	$V_{CE} = 5V, I_C = 0.5A, f = 1MHz$		20		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		210		pF

* h_{FE2} Rank classification

Rank	Q	S	P
h_{FE2}	60 to 120	80 to 160	100 to 200

$P_C - T_a$  $I_C - V_{CE}$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_C$  $C_{ob} - V_{CB}$ 

Area of safe operation (ASO)

